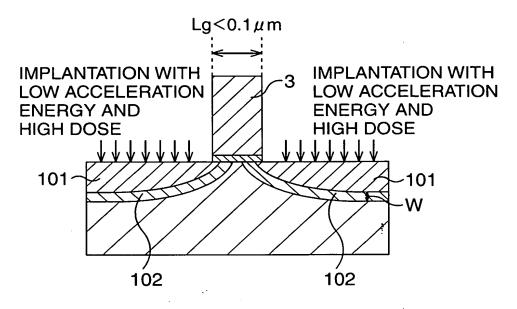
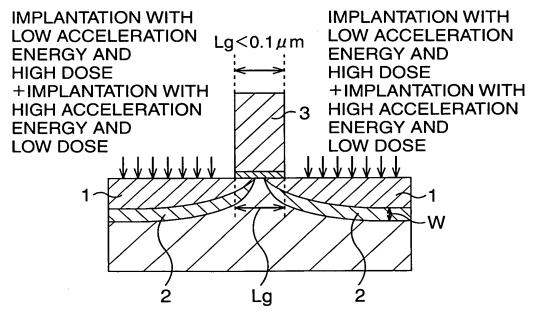


FIG. 2A



PRIOR ART

FIG. 2B



PRESENT INVENTION

FIG. 3

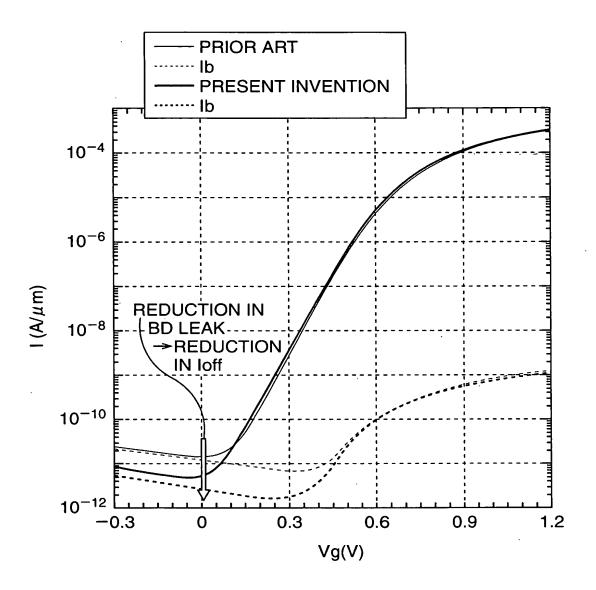


FIG. 4A

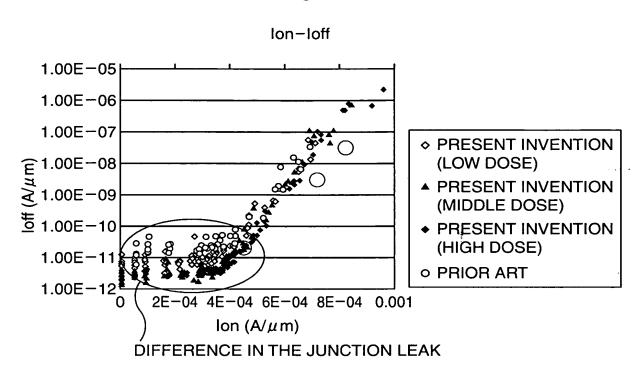


FIG. 4B

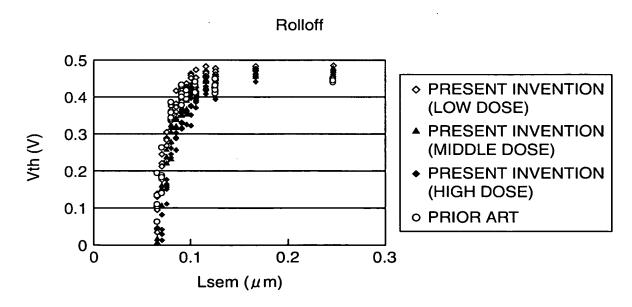
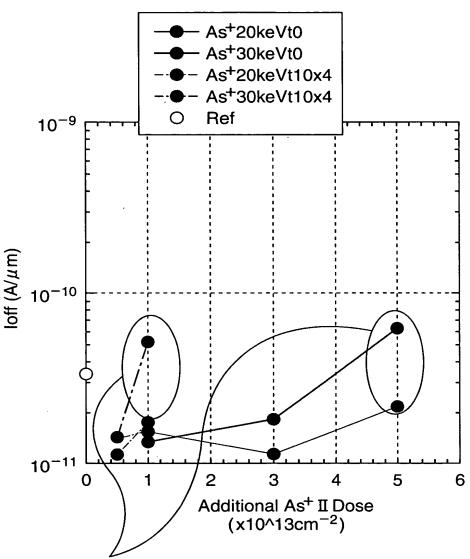


FIG. 5



INCREASE IN loff DUE TO DEGRADATION IN ROLL-OFF **CHARACTERISTIC**

Lg=80nm Vd=1.2V

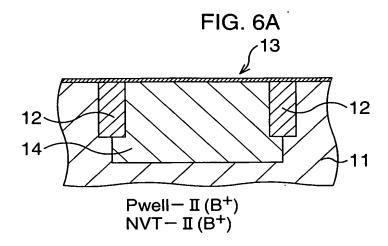


FIG. 6B

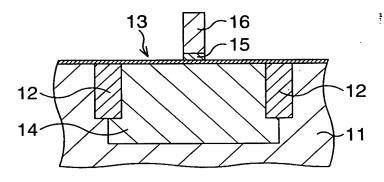


FIG. 6C

IMPLANTATION OF EXTENSION As+20~30keV1~3e13t0 +As+0.5~5keV0.5~2.5e15t0 (DOUBLE As+ IMPLANTATION)

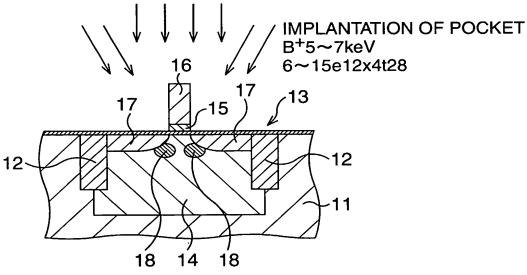


FIG. 7A

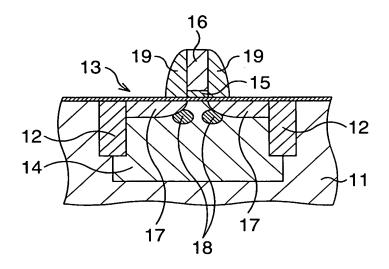


FIG. 7B

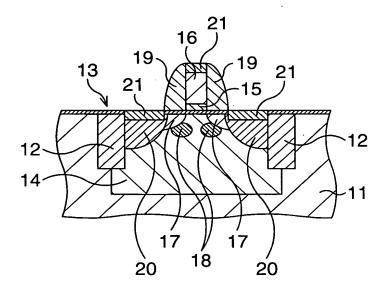
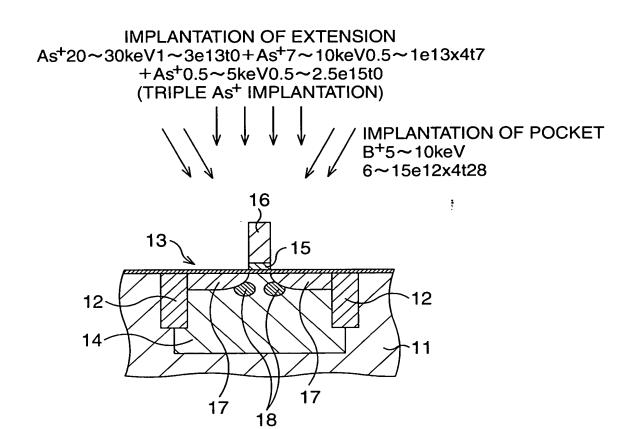


FIG. 8



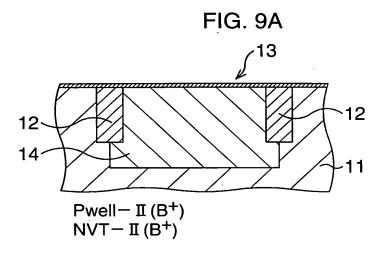


FIG. 9B

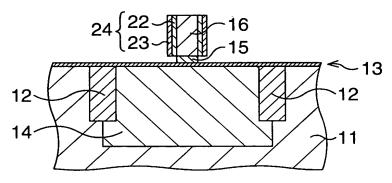


FIG. 9C

IMPLANTATION OF EXTENSION As+20~30keV1~3e13t0 +As+0.5~5keV0.5~2.5e15t0 (DOUBLE As+ IMPLANTATION)

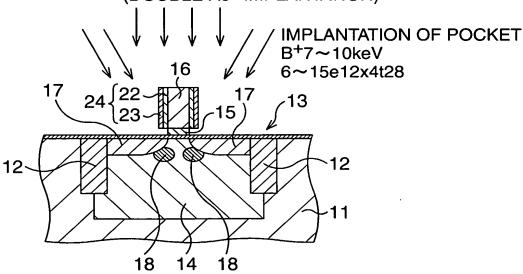


FIG. 10A

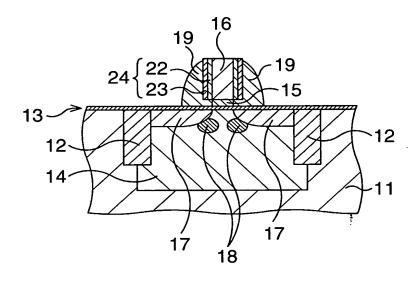


FIG. 10B

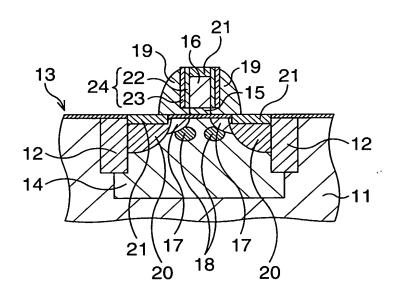
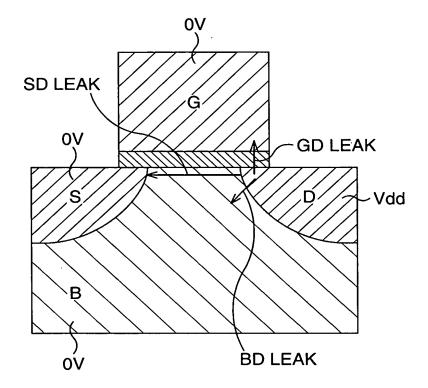


FIG. 11



Ioff=GD LEAK+SD LEAK+BD LEAK

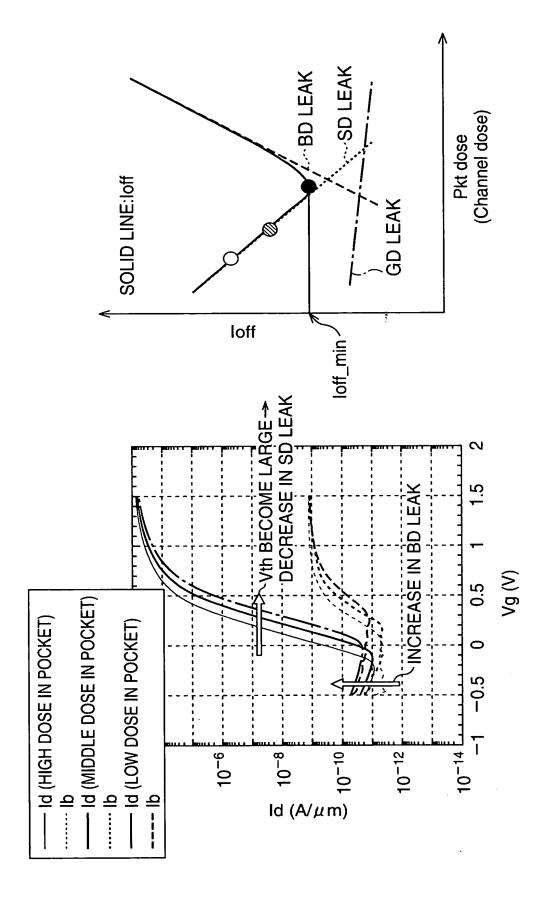


FIG. 12

FIG. 13

